

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Y. Long He et al.

Art Unit : 1763

Assignee : Intel Corporation

Examiner: George A. Goudreau

Serial No.: 10/076,129

Filed

: February 13, 2002

Title

PLASMA ETCHING UNIFORMITY CONTROL

Commissioner for Patents Washington, D.C. 20231

RESPONSE

THE CENTER TO TOO THE In response to the Office Action dated December 19, 2002, please amend the aboveidentified application as follows:

IN THE CLAIMS:

Please cancel claim 15.

Please amend claims 1, 6, 13, 16-18, 21, 22, 24, and 26, as follows:

-- 1. (Amended) A method, comprising:

providing a substrate material comprising a quartz plate;

providing a gas for generating a plasma, the gas including a first component and a second component selected such that varying the ratio of the first component to the second component varies the rate of etching of one location of the substrate relative to another location on the substrate;

generating the plasma; and using the plasma to etch the substrate material.

CERTIFICATE OF MAILING BY FIRST CLASS MAIL

I hereby certify under 37 CFR §1.8(a) that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage on the date indicated below and is addressed to the Commissioner for Patents, Washington, D.C. 20231.

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